

74LCX74**Low Voltage Dual D-Type
Positive Edge-Triggered Flip-Flop with 5V Tolerant Inputs****General Description**

The LCX74 is a dual D-type flip-flop with Asynchronous Clear and Set inputs and complementary (Q , \bar{Q}) outputs. Information at the input is transferred to the outputs on the positive edge of the clock pulse. After the Clock Pulse input threshold voltage has been passed, the Data input is locked out and information present will not be transferred to the outputs until the next rising edge of the Clock Pulse input.

Asynchronous Inputs:

LOW input to \bar{S}_D (Set) sets Q to HIGH level

LOW input to \bar{C}_D (Clear) sets Q to LOW level

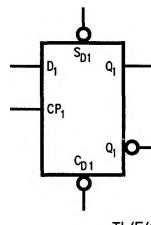
Clear and Set are independent of clock

Simultaneous LOW on \bar{C}_D and \bar{S}_D makes both Q and \bar{Q}

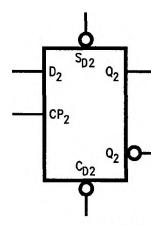
HIGH

Features

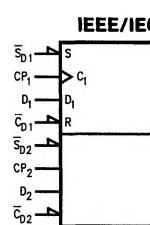
- 5V tolerant inputs
- 7.0 ns t_{PD} max, 10 μA I_{CCQ} max
- Power down high impedance inputs and outputs
- 2.0V–3.6V V_C supply operation
- ± 24 mA output drive
- Implements patented Quiet Series™ noise/EMI reduction circuitry
- Functionally compatible with 74 series 74
- Latch-up performance exceeds 500 mA
- ESD performance:
 - Human body model > 2000V
 - Machine model > 200V

Logic Symbols

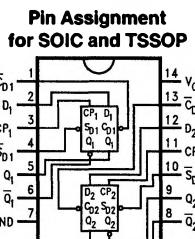
TL/F/12414-1



TL/F/12414-2



TL/F/12414-3

Connection Diagram

TL/F/12414-4

Truth Table (Each Half)

		Inputs				Outputs	
\bar{S}_D	\bar{C}_D	CP	D	Q	\bar{Q}		
L	H	X	X	H	L		
H	L	X	X	L	H		
L	L	X	X	H	H		
H	H	/	H	H	L		
H	H	/	L	L	H		
H	H	L	X	Q_0	\bar{Q}_0		

H = HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial

/ = LOW-to-HIGH Clock Transition

$Q_0(\bar{Q}_0)$ = Previous $Q(\bar{Q})$ before LOW-to-HIGH Transition of Clock

	SOIC JEDEC	SOIC EIAJ	TSSOP
Order Number	74LCX74M 74LCX74MX	74LCX74SJ 74LCX74SJX	74LCX74MTC 74LCX74MTCX
See NS Package Number	M14A	M14D	MTC14

Preliminary Data: National Semiconductor reserves the right to make changes at any time without notice.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Symbol	Parameter	Value	Conditions	Units
V _{CC}	Supply Voltage	−0.5 to +7.0		V
V _I	DC Input Voltage	−0.5 to +7.0		V
V _O	DC Output Voltage	−0.5 to V _{CC} + 0.5	Output in High or Low State (Note 2)	V
I _{IK}	DC Input Diode Current	−50	V _I < GND	mA
I _{OK}	DC Output Diode Current	−50 +50	V _O < GND V _O > V _{CC}	mA
I _O	DC Output Source/Sink Current	±50		mA
I _{CC}	DC Supply Current per Supply Pin	±100		mA
I _{GND}	DC Ground Current per Ground Pin	±100		mA
T _{TSG}	Storage Temperature	−65 to +150		°C

Note 1: The Absolute Maximum Ratings are those values beyond which the safety of the device cannot be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the Absolute Maximum Ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Note 2: I_O Absolute Maximum Rating must be observed.

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Units
V _{CC}	Supply Voltage	2.0	3.6	V
	Operating Data Retention	1.5	3.6	
V _I	Input Voltage	0	5.5	V
V _O	Output Voltage	HIGH or LOW State	0	V _{CC}
I _{OH} /I _{OL}	Output Current	V _{CC} = 3.0V – 3.6V V _{CC} = 2.7V	±24 ±12	mA
T _A	Free-Air Operating Temperature	−40	85	°C
Δt/ΔV	Input Edge Rate, V _{IN} = 0.8V–2.0V, V _{CC} = 3.0V	0	10	ns/V

DC Electrical Characteristics

Symbol	Parameter	Conditions	V _{CC} (V)	T _A = −40°C to +85°C		Units
				Min	Max	
V _{IH}	HIGH Level Input Voltage		2.7–3.6	2.0		V
V _{IL}	LOW Level Input Voltage		2.7–3.6		0.8	V
V _{OH}	HIGH Level Output Voltage	I _{OH} = −100 μA	2.7–3.6	V _{CC} – 0.2		V
		I _{OH} = −12 mA	2.7	2.2		V
		I _{OH} = −18 mA	3.0	2.4		V
		I _{OH} = −24 mA	3.0	2.2		V
V _{OL}	LOW Level Output Voltage	I _{OL} = 100 μA	2.7–3.6		0.2	V
		I _{OL} = 12 mA	2.7		0.4	V
		I _{OL} = 16 mA	3.0		0.4	V
		I _{OL} = 24 mA	3.0		0.55	V
I _I	Input Leakage Current	0 ≤ V _I ≤ 5.5V	2.7–3.6		±5.0	μA
I _{OFF}	Power-Off Leakage Current	V _I or V _O = 5.5V	0		100	μA
I _{CC}	Quiescent Supply Current	V _I = V _{CC} or GND	2.7–3.6		10	μA
		3.6V ≤ V _I , V _O ≤ 5.5V	2.7–3.6		±10	μA
ΔI _{CC}	Increase in I _{CC} per Input	V _{IH} = V _{CC} − 0.6V	2.7–3.6		500	μA

AC Electrical Characteristics (Preliminary)

Symbol	Parameter	$T_A = -40^\circ\text{C to } +85^\circ\text{C}$				Units	
		$V_{CC} = 3.3V \pm 0.3V$		$V_{CC} = 2.7V$			
		Min	Max	Min	Max		
f_{MAX}	Maximum Clock Frequency	150				MHz	
t_{PHL}	Propagation Delay CP to Q	1.5	7.0	1.5	8.0	ns	
t_{PLH}	Propagation Delay S/R	1.5	7.0	1.5	8.0	ns	
t_S	Setup Time	2.5		2.5		ns	
t_H	Hold Time	1.5		1.5		ns	
t_W	Pulse Width CP and S/R	3.3		3.3		ns	
t_{rem}	Removal Time	0.0		0.0		ns	
t_{OSHL} t_{OSLH}	Output to Output Skew (Note 1)		1.0			ns	
			1.0				

Note 1: Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH to LOW (t_{OSHL}) or LOW to HIGH (t_{OSLH}).

Dynamic Switching Characteristics

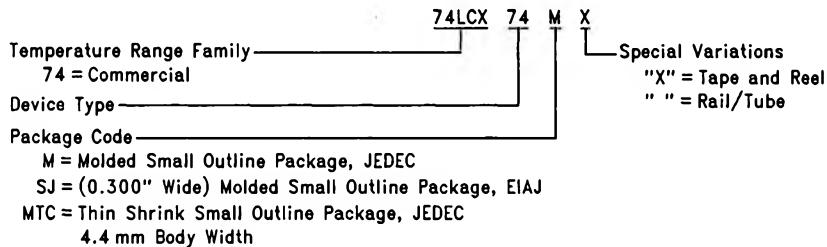
Symbol	Parameter	Conditions	V_{CC} (V)	$T_A = 25^\circ\text{C}$	Unit
				Typical	
V_{OLP}	Quiet Output Dynamic Peak V_{OL}	$C_L = 50 \text{ pF}, V_{IH} = 3.3V, V_{IL} = 0V$	3.3	0.8	V
V_{OLV}	Quiet Output Dynamic Valley V_{OL}	$C_L = 50 \text{ pF}, V_{IH} = 3.3V, V_{IL} = 0V$	3.3	0.8	V

Capacitance

Symbol	Parameter	Conditions	Typical	Units
C_{IN}	Input Capacitance	$V_{CC} = \text{Open}, V_I = 0V \text{ or } V_{CC}$	7	pF
C_{OUT}	Output Capacitance	$V_{CC} = 3.3V, V_I = 0V \text{ or } V_{CC}$	8	pF
C_{PD}	Power Dissipation Capacitance	$V_{CC} = 3.3V, V_I = 0V \text{ or } V_{CC}, f = 10 \text{ MHz}$	25	pF

74LCX74 Ordering Information

The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:



LCX74

TL/F/12414-5